

Hilde H Hardtdegen

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

205
papers

2,733
citations

29
h-index

40
g-index

244
ext. papers

3,009
ext. citations

2.8
avg, IF

4.63
L-index

#	Paper	IF	Citations
205	Cutting-edge nano-LED technology. <i>Journal of Applied Physics</i> , 2022 , 131, 110903	2.5	2
204	Electron transport in AlGa _N /Ga _N HEMT-like nanowires: Effect of depletion and UV excitation. <i>Semiconductor Physics, Quantum Electronics and Optoelectronics</i> , 2021 , 24, 407-412	0.4	
203	Generation of terahertz transients from Co ₂ Fe _{0.4} Mn _{0.6} Si Heusler alloy/heavy-metal bilayers. <i>Journal of Magnetism and Magnetic Materials</i> , 2021 , 547, 168791	2.8	
202	Generation of terahertz transients from Co ₂ Fe _{0.4} Mn _{0.6} Si-Heusler-alloy/normal-metal nanobilayers excited by femtosecond optical pulses. <i>Physical Review Research</i> , 2021 , 3,	3.9	2
201	Conditioning nano-LEDs in arrays by laser-micro-annealing: The key to their performance improvement. <i>Applied Physics Letters</i> , 2021 , 118, 043101	3.4	7
200	Local increase in compressive strain (Ga _N) in gate recessed AlGa _N /Ga _N MISHFET structures induced by an amorphous Al _N dielectric layer. <i>Semiconductor Science and Technology</i> , 2021 , 36, 095040	1.8	2
199	Nano-LED induced chemical reactions for structuring processes. <i>Nanoscale Advances</i> , 2020 , 2, 5421-5427	5.1	6
198	Fully photon operated transmistor / all-optical switch based on a layered Ge ₁ Sb ₂ Te ₄ phase change medium. <i>FlatChem</i> , 2020 , 23, 100186	5.1	14
197	Laser micro annealing conditioning for the suppression of statistical scatter in freestanding Sb ₂ Te ₃ nanowire resistance. <i>FlatChem</i> , 2020 , 21, 100164	5.1	11
196	Magnetically and optically tunable terahertz radiation from Ta/NiFe/Pt spintronic nanolayers generated by femtosecond laser pulses. <i>Applied Physics Letters</i> , 2019 , 114, 212405	3.4	17
195	Column III 2019 , 71-108		
194	Visualization and investigation of the non-thermalized electrons in an InAs nanowire by scanning gate microscopy. <i>Journal of Physics Condensed Matter</i> , 2019 , 31, 415302	1.8	1
193	Electric Current and Noise in Long Ga _N Nanowires in the Space-Charge Limited Transport Regime. <i>Fluctuation and Noise Letters</i> , 2017 , 16, 1750010	1.2	2
192	Electronic edge-state and space-charge phenomena in long Ga _N nanowires and nanoribbons. <i>Nanotechnology</i> , 2017 , 28, 135204	3.4	7
191	The Covalent Functionalization of Layered Black Phosphorus by Nucleophilic Reagents. <i>Angewandte Chemie - International Edition</i> , 2017 , 56, 9891-9896	16.4	124
190	Efficient heat dissipation in AlGa _N /Ga _N heterostructure grown on silver substrate. <i>Applied Materials Today</i> , 2017 , 7, 134-137	6.6	23
189	Stability of charged density waves in InAs nanowires in an external magnetic field. <i>Journal of Physics Condensed Matter</i> , 2017 , 29, 475601	1.8	2

188	Experimental determination of Rashba and Dresselhaus parameters and g^* -factor anisotropy via Shubnikov-de Haas oscillations. <i>New Journal of Physics</i> , 2017 , 19, 103012	2.9	8
187	Nano-light-emitting-diodes based on InGaN mesoscopic structures for energy saving optoelectronics. <i>Applied Physics Letters</i> , 2016 , 109, 041103	3.4	21
186	Compact extreme ultraviolet source for laboratory-based photoemission spectromicroscopy. <i>Applied Physics Letters</i> , 2016 , 108, 234101	3.4	7
185	Towards III-nitride nano-LED based single photon emitters: Technology and applications 2016 ,		1
184	Electrical and optical characterization of freestanding Ge ₁ Sb ₂ Te ₄ nano-membranes integrated in coplanar strip lines 2016 ,		8
183	Direct electro-optical pumping for hybrid CdSe nanocrystal/III-nitride based nano-light-emitting diodes. <i>Applied Physics Letters</i> , 2016 , 108, 061107	3.4	36
182	Confinement and inhomogeneous broadening effects in the quantum oscillatory magnetization of quantum dot ensembles. <i>Journal of Physics Condensed Matter</i> , 2016 , 28, 045301	1.8	2
181	Hybrid optoelectronics based on a nanocrystal/III-N nano-LED platform 2016 ,		5
180	InGaN mesoscopic structures for low energy consumption nano-opto-electronics 2016 ,		1
179	A model structure for interfacial phase change memories: Epitaxial trigonal Ge ₁ Sb ₂ Te ₄ . <i>Journal of Alloys and Compounds</i> , 2016 , 679, 285-292	5.7	37
178	Dense, Regular GaAs Nanowire Arrays by Catalyst-Free Vapor Phase Epitaxy for Light Harvesting. <i>ACS Applied Materials & Interfaces</i> , 2016 , 8, 22484-92	9.5	2
177	Metal organic vapor phase epitaxy of hexagonal Ge ₂ Sb ₂ Te ₅ (GST). <i>Journal of Crystal Growth</i> , 2015 , 420, 37-41	1.6	12
176	Nano-LED array fabrication suitable for future single photon lithography. <i>Nanotechnology</i> , 2015 , 26, 185302	3.4	36
175	Resolving ambiguities in nanowire field-effect transistor characterization. <i>Nanoscale</i> , 2015 , 7, 18188-97	7.7	25
174	Polymorphous GdScO ₃ as high permittivity dielectric. <i>Journal of Alloys and Compounds</i> , 2015 , 651, 514-520	3.9	6
173	Correlations of the mutual positions of the nodes of charge density waves in side-by-side placed InAs wires measured with scanning gate microscopy. <i>JETP Letters</i> , 2015 , 101, 628-632	1.2	4
172	Micromechanical measurement of beating patterns in the quantum oscillatory chemical potential of InGaAs quantum wells due to spin-orbit coupling. <i>Applied Physics Letters</i> , 2015 , 107, 092101	3.4	2
171	Modern chemical synthesis methods towards low-dimensional phase change structures in the Ge ₂ Sb ₂ Te ₅ material system. <i>Progress in Crystal Growth and Characterization of Materials</i> , 2015 , 61, 27-45	3.5	39

170	Hexagonal LaLuO ₃ as high- ϵ dielectric. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2015 , 33, 01A104	1.3	3
169	High-field quasi-ballistic transport in AlGa _N /Ga _N heterostructures. <i>Applied Physics Letters</i> , 2014 , 104, 072105	3.4	7
168	Magnetic properties of Gd-doped Ga _N . <i>Physica Status Solidi (B): Basic Research</i> , 2014 , 251, 1673-1684	1.3	11
167	Evolution and characteristics of Ga _N nanowires produced via maskless reactive ion etching. <i>Nanotechnology</i> , 2014 , 25, 255301	3.4	8
166	Crossover from Josephson effect to single interface Andreev reflection in asymmetric superconductor/nanowire junctions. <i>Nano Letters</i> , 2014 , 14, 4977-81	11.5	19
165	The Role of Si during the Growth of Ga _N Micro- and Nanorods. <i>Crystal Growth and Design</i> , 2014 , 14, 14863-1492	3.4	66
164	Investigations of local electronic transport in InAs nanowires by scanning gate microscopy at liquid helium temperatures. <i>JETP Letters</i> , 2014 , 100, 32-38	1.2	6
163	Reduction of skin effect losses in double-level-T-gate structure. <i>Applied Physics Letters</i> , 2014 , 105, 232102	3.4	2
162	III-nitride nano-LEDs for single photon lithography 2014 ,		1
161	Quantum dots in InAs nanowires induced by surface potential fluctuations. <i>Nanotechnology</i> , 2014 , 25, 135203	3.4	7
160	Hexagonal GdScO ₃ : an epitaxial high- ϵ dielectric for Ga _N . <i>Semiconductor Science and Technology</i> , 2014 , 29, 075005	1.8	5
159	The electronic transport of top subband and disordered sea in an InAs nanowire in the presence of a mobile gate. <i>Journal of Physics Condensed Matter</i> , 2014 , 26, 165304	1.8	6
158	Impact of thermal annealing on nonequilibrium carrier dynamics in single-crystal, freestanding GaAs mesostructures. <i>Semiconductor Science and Technology</i> , 2014 , 29, 045022	1.8	5
157	Frequency anomaly in the Rashba-effect induced magnetization oscillations of a high-mobility two-dimensional electron system. <i>Physical Review B</i> , 2013 , 87,	3.3	9
156	Site-controlled growth of indium nitride based nanostructures using metalorganic vapour phase epitaxy. <i>Journal of Crystal Growth</i> , 2013 , 370, 336-341	1.6	15
155	Nanoimprint and selective-area MOVPE for growth of GaAs/InAs core/shell nanowires. <i>Nanotechnology</i> , 2013 , 24, 085603	3.4	42
154	Distortions of the coulomb blockade conductance line in scanning gate measurements of InAs nanowire based quantum dots. <i>Journal of Experimental and Theoretical Physics</i> , 2013 , 116, 138-144	1	6
153	From conformal overgrowth to lateral growth of indium arsenide nano structures on silicon substrates by MOVPE. <i>Journal of Crystal Growth</i> , 2013 , 370, 141-145	1.6	5

152	Long electron spin coherence in ion-implanted GaN: The role of localization. <i>Applied Physics Letters</i> , 2013 , 102, 192102	3.4	13
151	Vertically integrated (Ga, In)N nanostructures for future single photon emitters operating in the telecommunication wavelength range. <i>Nanotechnology</i> , 2013 , 24, 405302	3.4	7
150	Realization of nanoscaled tubular conductors by means of GaAs/InAs core/shell nanowires. <i>Nanotechnology</i> , 2013 , 24, 035203	3.4	35
149	Inhomogeneity of donor doping in SrTiO ₃ substrates studied by fluorescence-lifetime imaging microscopy. <i>Applied Physics Letters</i> , 2013 , 103, 162904	3.4	15
148	Spectral Sensitivity Tuning of Vertical InN Nanopyramid-Based Photodetectors. <i>Japanese Journal of Applied Physics</i> , 2013 , 52, 08JF05	1.4	9
147	Highly Transparent Conducting Polymer Top Contacts for Future III-Nitride Based Single Photon Emitters. <i>Japanese Journal of Applied Physics</i> , 2013 , 52, 08JH10	1.4	4
146	Electrical spin injection into InN semiconductor nanowires. <i>Nano Letters</i> , 2012 , 12, 4437-43	11.5	31
145	Direct observation of standing electron waves in diffusively conducting InAs nanowire. <i>JETP Letters</i> , 2012 , 96, 109-112	1.2	5
144	Negative differential conductance in InAs wire based double quantum dot induced by a charged AFM tip. <i>Journal of Experimental and Theoretical Physics</i> , 2012 , 115, 1062-1067	1	4
143	Comparison of InAs nanowire conductivity: influence of growth method and structure. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012 , 9, 230-234		7
142	Self-assembled GaN nanostructures by dry etching and their optical properties. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2012 , 209, 443-446	1.6	6
141	Residual strain in recessed AlGaIn/GaN heterostructure field-effect transistors evaluated by micro photoluminescence measurements. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012 , 9, 911-914		4
140	Morphology evolution and optical properties of GaN nano-pyramids grown by selective area MOVPE. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012 , 9, 624-627		4
139	Photoluminescence and Raman scattering studies of GaN nanowires obtained by top-down and bottom-up approaches. <i>Materials Research Society Symposia Proceedings</i> , 2012 , 1408, 29		2
138	Scanning tunneling microscopy with InAs nanowire tips. <i>Applied Physics Letters</i> , 2012 , 101, 243101	3.4	4
137	Monitoring structural influences on quantum transport in InAs nanowires. <i>Applied Physics Letters</i> , 2012 , 101, 062104	3.4	5
136	Supercurrent in Nb/InAs-nanowire/Nb Josephson junctions. <i>Journal of Applied Physics</i> , 2012 , 112, 034316.5	16.5	29
135	Non-uniform distribution of induced strain in a gate-recessed AlGaIn/GaN structure evaluated by micro-PL measurements. <i>Semiconductor Science and Technology</i> , 2012 , 27, 105008	1.8	11

134	Preparation of Ohmic contacts to GaAs/AlGaAs-core/shell-nanowires. <i>Applied Physics Letters</i> , 2012 , 100, 042103	3.4	12
133	Effect of Si-doping on InAs nanowire transport and morphology. <i>Journal of Applied Physics</i> , 2011 , 110, 053709	2.5	55
132	Low-temperature conductance of the weak junction in InAs nanowire in the field of AFM scanning gate. <i>JETP Letters</i> , 2011 , 93, 10-14	1.2	10
131	New method of creation of a rearrangeable local Coulomb potential profile and its application for investigations of local conductivity of InAs nanowires. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2011 , 44, 690-695	3	5
130	Manipulating InAs nanowires with submicrometer precision. <i>Review of Scientific Instruments</i> , 2011 , 82, 113705	1.7	28
129	Magnetism in GaN layers implanted by La, Gd, Dy and Lu. <i>Thin Solid Films</i> , 2011 , 519, 6120-6125	2.2	10
128	Influence of silicon doping on the SA-MOVPE of InAs nanowires. <i>Materials Research Society Symposia Proceedings</i> , 2010 , 1258, 1		3
127	LaLuO ₃ as a high-k gate dielectric for InAs nanowire structures. <i>Semiconductor Science and Technology</i> , 2010 , 25, 085001	1.8	5
126	Femtosecond and highly sensitive GaAs metal-semiconductor-metal photodetectors grown on aluminum mirrors/pseudo-substrates. <i>Semiconductor Science and Technology</i> , 2010 , 25, 075001	1.8	10
125	Spin-orbit coupling and phase coherence in InAs nanowires. <i>Physical Review B</i> , 2010 , 82,	3.3	74
124	Improved gate-control in InAs nanowire structures by the use of GdScO ₃ as a gate dielectric. <i>Applied Physics A: Materials Science and Processing</i> , 2010 , 100, 305-308	2.6	1
123	MOVPE of n-doped GaAs and modulation doped GaAs/AlGaAs nanowires. <i>Journal of Crystal Growth</i> , 2010 , 312, 635-640	1.6	36
122	Nanowires: Technology, Physics and Perspectives 2010 , 171-181		
121	Strain-enhanced electron mobility anisotropy in In _x Ga _{1-x} As/InP two-dimensional electron gases. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2010 , 42, 1130-1133	3	3
120	g-factor and exchange energy in a few-electron lateral InGaAs quantum dot. <i>Applied Physics Letters</i> , 2009 , 95, 192112	3.4	8
119	Origin and limiting mechanism of induced nonequilibrium currents in gated two-dimensional electron systems. <i>Physical Review B</i> , 2009 , 80,	3.3	8
118	Gate-defined quantum-dot devices realized in InGaAs/InP by incorporating a HfO ₂ layer as gate dielectric. <i>Applied Physics Letters</i> , 2009 , 94, 042114	3.4	17
117	Spin-orbit coupling in Ga _x In _{1-x} As/InP two-dimensional electron gases and quantum wire structures. <i>Semiconductor Science and Technology</i> , 2009 , 24, 064001	1.8	11

116	In-situ doping and implantation of GaN layers with Mn. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009 , 6, S646-S649		4
115	Study on growth and electrical performance of double-heterostructure AlGaIn/GaN/AlGaIn field-effect-transistors. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009 , 6, S1003-S1006		5
114	Influence of growth temperature on the selective area MOVPE of InAs nanowires on GaAs (1 1 1) B using N ₂ carrier gas. <i>Journal of Crystal Growth</i> , 2009 , 311, 3813-3816	1.6	32
113	Influence of growth temperature on GaN:Cr incorporation and structural properties in MOVPE. <i>Journal of Crystal Growth</i> , 2009 , 312, 1-9	1.6	8
112	Electronic transport in mesoscopic superconductor/2D electron gas junctions in strong magnetic field. <i>Bulletin of the Russian Academy of Sciences: Physics</i> , 2009 , 73, 880-882	0.4	
111	Quantum confinement effect on the effective mass in two-dimensional electron gas of AlGaIn/GaN heterostructures. <i>Journal of Applied Physics</i> , 2009 , 105, 073703	2.5	28
110	Mechanism of strain relaxation by twisted nanocolumns revealed in AlGaIn/GaN heterostructures. <i>Applied Physics Letters</i> , 2009 , 95, 031907	3.4	14
109	Internal strains and crystal structure of the layers in AlGaIn/GaN heterostructures grown on a sapphire substrate. <i>Journal of Applied Physics</i> , 2009 , 105, 063515	2.5	32
108	InGaInAs/InP selective area metal-organic vapor phase epitaxy for non-magnetic semiconductor spintronics. <i>Journal of Crystal Growth</i> , 2008 , 310, 4821-4825	1.6	1
107	On the magnetic properties of Gd implanted GaN. <i>Journal of Applied Physics</i> , 2008 , 103, 07D107	2.5	28
106	Mechanism of mobility increase of the two-dimensional electron gas in AlGaIn/GaN heterostructures under small dose gamma irradiation. <i>Journal of Applied Physics</i> , 2008 , 103, 083707	2.5	43
105	Weak antilocalization in high mobility GaInAs/InP two-dimensional electron gases with strong spin-orbit coupling. <i>Physical Review B</i> , 2007 , 76,	3.3	36
104	Investigation of AlN growth on sapphire substrates in a horizontal MOVPE reactor. <i>Journal of Physics and Chemistry of Solids</i> , 2007 , 68, 1131-1134	3.9	1
103	Influence of the reactor inlet configuration on the AlGaIn growth efficiency. <i>Journal of Crystal Growth</i> , 2007 , 298, 413-417	1.6	5
102	The growth mechanism of GaN with different H ₂ /N ₂ carrier gas ratios. <i>Journal of Crystal Growth</i> , 2007 , 307, 6-13	1.6	11
101	The growth of Cr-doped GaN by MOVPE towards spintronic applications. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2007 , 204, 72-77	1.6	3
100	Rashba effect in GaIn _{1-x} As/InP quantum wire structures. <i>Applied Physics A: Materials Science and Processing</i> , 2007 , 87, 577-584	2.6	10
99	New approaches for growth control of GaN-based HEMT structures. <i>Applied Physics A: Materials Science and Processing</i> , 2007 , 87, 491-498	2.6	2

98	Suppression of weak antilocalization in an $\text{Al}_x\text{Ga}_{1-x}\text{N}/\text{GaN}$ two-dimensional electron gas by an in-plane magnetic field. <i>Physical Review B</i> , 2007 , 75,	3-3	6
97	Andreev reflection and strongly enhanced magnetoresistance oscillations in $\text{Ga}_x\text{In}_{1-x}\text{As}/\text{InP}$ heterostructures with superconducting contacts. <i>Physical Review B</i> , 2007 , 76,	3-3	22
96	Intra-atomic photoluminescence at 1.41 eV of substitutional Mn in GaMnN of high optical quality. <i>Journal of Applied Physics</i> , 2007 , 101, 063504	2.5	22
95	Zeeman splitting in ballistic GaInAs/InP split-gate quantum point contacts. <i>Applied Physics Letters</i> , 2007 , 90, 122107	3-4	14
94	Enhanced spin-orbit scattering length in narrow $\text{Al}_x\text{Ga}_{1-x}\text{N}/\text{GaN}$ wires. <i>Physical Review B</i> , 2007 , 76,	3-3	33
93	Weak antilocalization in gate-controlled $\text{Al}_x\text{Ga}_{1-x}\text{N}/\text{GaN}$ two-dimensional electron gases. <i>Physical Review B</i> , 2006 , 73,	3-3	47
92	Rashba effect in InGaAs/InP parallel quantum wires. <i>Applied Physics Letters</i> , 2006 , 88, 032102	3-4	29
91	Suppression of weak antilocalization in $\text{Ga}_x\text{In}_{1-x}\text{As}/\text{InP}$ narrow quantum wires. <i>Physical Review B</i> , 2006 , 74,	3-3	59
90	The state of strain in single GaN nanocolumns as derived from micro-photoluminescence measurements. <i>Nano Letters</i> , 2006 , 6, 704-8	11.5	96
89	Weak antilocalization in a polarization-doped $\text{Al}_x\text{Ga}_{1-x}\text{N}/\text{GaN}$ heterostructure with single subband occupation. <i>Applied Physics Letters</i> , 2006 , 88, 022111	3-4	49
88	Observation of growth during the MOVPE of III-nitrides. <i>European Physical Journal Special Topics</i> , 2006 , 132, 177-183		3
87	Effect of carrier gas on GaN epilayer characteristics. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006 , 3, 1408-1411		43
86	Spin-orbit coupling in gated AlGaIn/GaN 2-dimensional electron gases. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006 , 3, 4247-4250		2
85	New method for the in situ determination of $\text{Al}_x\text{Ga}_{1-x}\text{N}$ composition in MOVPE by real-time optical reflectance. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2006 , 203, 1645-1649	1.6	2
84	Epitaxial growth and characterization of Fe thin films on wurtzite $\text{GaN}(0001)$. <i>Journal of Crystal Growth</i> , 2005 , 283, 500-507	1.6	22
83	Uniform III-nitride growth in single wafer horizontal MOVPE reactors. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2005 , 202, 744-748	1.6	10
82	Use of wafer temperature determination for the study of unintentional parameter influences for the MOVPE of III-nitrides. <i>Physica Status Solidi (B): Basic Research</i> , 2005 , 242, 2581-2586	1-3	7
81	Shot noise of large charge quanta in superconductor/semiconductor/superconductor junctions. <i>Physical Review B</i> , 2005 , 71,	3-3	5

80	MOVPE process for horizontal reactors with reduced parasitic deposition. <i>Journal of Crystal Growth</i> , 2004 , 272, 407-414	1.6	15
79	MOVPE growth and in situ characterization of GaN layers on sapphire substrates. <i>Physica Status Solidi A</i> , 2004 , 201, 312-319		17
78	MOVPE GaN growth: determination of activation energy using in-situ reflectometry. <i>Journal of Crystal Growth</i> , 2004 , 272, 100-105	1.6	10
77	Use of SiC band gap temperature dependence for absolute calibration of emissivity corrected pyrometers in III-nitride MOVPE. <i>Journal of Crystal Growth</i> , 2004 , 272, 81-86	1.6	9
76	Supercurrent control in a multi-terminal Nb-InGaAs/InP junction with Nb injector electrodes. <i>Superconductor Science and Technology</i> , 2003 , 16, 714-719	3.1	1
75	Rashba effect in strained InGaAs/InP quantum wire structures. <i>Science and Technology of Advanced Materials</i> , 2003 , 4, 19-25	7.1	12
74	Homogeneity analysis of ion-implanted resonant tunnelling diodes for applications in digital logic circuits. <i>Superlattices and Microstructures</i> , 2002 , 31, 315-325	2.8	1
73	Real-time calibration of wafer temperature, growth rate and composition by optical in-situ techniques during Al _x Ga _{1-x} As growth in MOVPE. <i>Journal of Crystal Growth</i> , 2002 , 240, 87-97	1.6	26
72	On the suitability of getter-purified hydrogen for the LP-MOVPE of (AlGa)As: A comparison to Pd-diffused hydrogen. <i>Journal of Electronic Materials</i> , 2001 , 30, 1397-1401	1.9	2
71	AlGa _N /Ga _N HEMT Optimization Using the RoundHEMT Technology. <i>Physica Status Solidi A</i> , 2001 , 188, 199-202		3
70	The Influence of Nucleation Parameters on GaN Buffer Layer Properties Used for HEMT Application. <i>Physica Status Solidi A</i> , 2001 , 188, 647-651		1
69	On the influence of gas inlet configuration with respect to homogeneity in a horizontal single wafer MOVPE reactor. <i>Journal of Crystal Growth</i> , 2001 , 223, 15-20	1.6	12
68	Modeling and experimental verification of deposition behavior during AlGaAs growth: a comparison for the carrier gases N ₂ and H ₂ . <i>Journal of Crystal Growth</i> , 2001 , 223, 21-28	1.6	29
67	Chemical Vapor Epitaxy of Al _x Ga _{1-x} As 2001 , 1187-1191		
66	AlGa _N /Ga _N Round-HEMTs on (111) silicon substrates. <i>Electronics Letters</i> , 2001 , 37, 1364	1.1	6
65	On the choice of precursors for the MOVPE-growth of high-quality Al _{0.30} Ga _{0.70} As/GaAs v-groove quantum wires with large subband spacing. <i>Journal of Crystal Growth</i> , 2000 , 221, 91-97	1.6	8
64	Electron transport in modulation-doped GaAs v-groove quantum wires. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2000 , 7, 760-765	3	8
63	Fermi-edge singularities in the photoluminescence and magneto-optical spectra of modulation-doped v-groove quantum wires. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2000 , 6, 530-533	3	2

62	Fermi-edge singularities in the photoluminescence spectrum of modulation-doped GaAs v-groove quantum wires. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2000 , 7, 517-520	3	2
61	Preparation of transparent Nb/two-dimensional electron gas contacts by using electron cyclotron resonance plasma cleaning. <i>Journal of Applied Physics</i> , 2000 , 88, 4440	2.5	4
60	Direct determination of the Andreev reflection probability by means of point contact spectroscopy. <i>Applied Physics Letters</i> , 2000 , 76, 1152-1154	3.4	14
59	Adjustment of the critical current in a Nb _{1-x} Ga _{1-x} As/InP Josephson contact by light exposure. <i>Applied Physics Letters</i> , 1999 , 75, 391-393	3.4	9
58	Optical and transport studies of hot electrons in modulation-doped quantum wires. <i>Physica B: Condensed Matter</i> , 1999 , 272, 101-106	2.8	4
57	MOMBE and characterization of InAs and (Al,Ga)Sb. <i>Journal of Crystal Growth</i> , 1998 , 188, 32-38	1.6	3
56	Deep-level states in MOVPE AlGaAs. <i>Journal of Crystal Growth</i> , 1998 , 186, 13-20	1.6	6
55	Contributions to understanding the optical properties of partially ordered (Al _{0.3} Ga _{0.7}) _{0.52} In _{0.48} P. <i>Journal of Crystal Growth</i> , 1998 , 195, 124-131	1.6	3
54	In situ characterization of GaAs growth in nitrogen atmosphere during MOVPE: a comparison to hydrogen atmosphere. <i>Journal of Crystal Growth</i> , 1998 , 195, 211-216	1.6	27
53	Electrical and structural studies of AlGaAs/GaAs wires grown on patterned substrates. <i>Applied Surface Science</i> , 1998 , 123-124, 687-693	6.7	8
52	Optoelectronic d.c. and r.f. behavior of InP/InGaAs based HEMTs. <i>Solid-State Electronics</i> , 1998 , 42, 197-200	7	3
51	Electron states, magneto-transport and carrier dynamics in modulation-doped V-groove quantum wires. <i>Solid-State Electronics</i> , 1998 , 42, 1245-1249	1.7	7
50	MOVPE gets green signal. <i>III-Vs Review</i> , 1998 , 11, 34-39		2
49	Spontaneous formation of a tilted AlGaAs/GaAs superlattice during AlGaAs growth. <i>Applied Surface Science</i> , 1998 , 123-124, 704-709	6.7	
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